

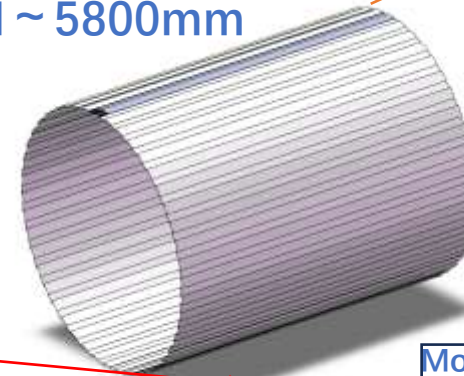
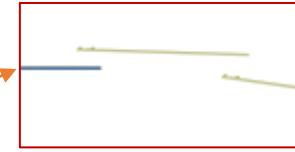
outer tracker 方案和成本估算 (以LGAD为例)

严雄波, 魏微, 胡俊, 史欣, 梁志均

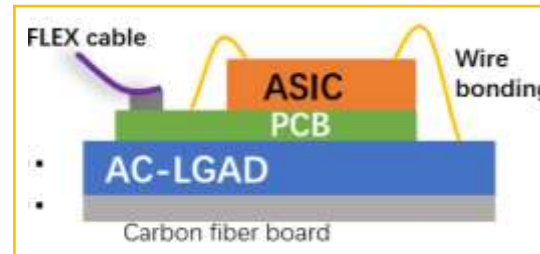
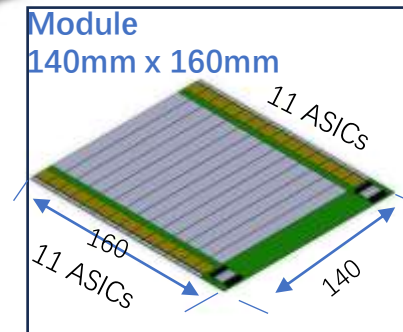
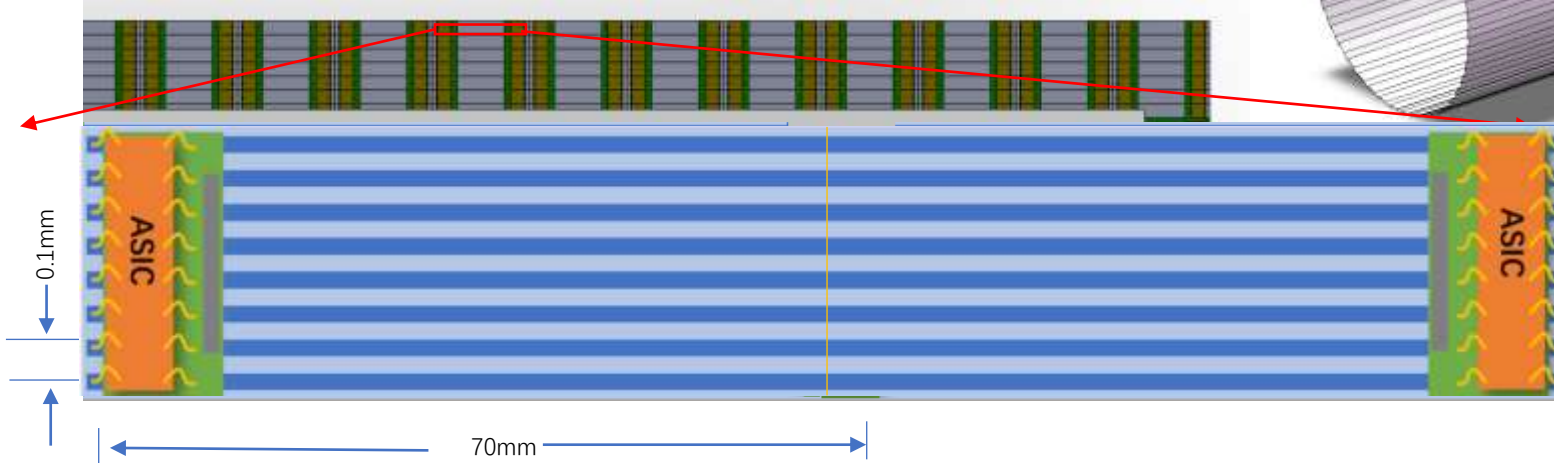
Arrangement of the ToF with strip LGAD

- One layer:
 - 90 ladders, 45 ladders each side,
 - ◆ 42 modules/ladder
 - 22 ASIC/module
 - ✓ 128 channels/ASIC
- Total modules needed:
 $45 * 2 * 42 = 3780$ modules

One layer ToF
 $R = 1800$ mm
 $H \sim 5800$ mm



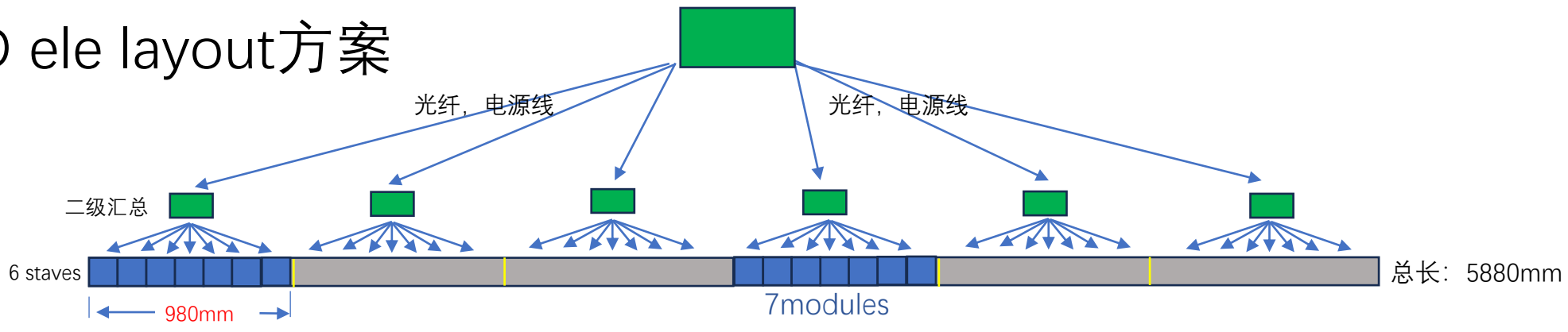
Ladder



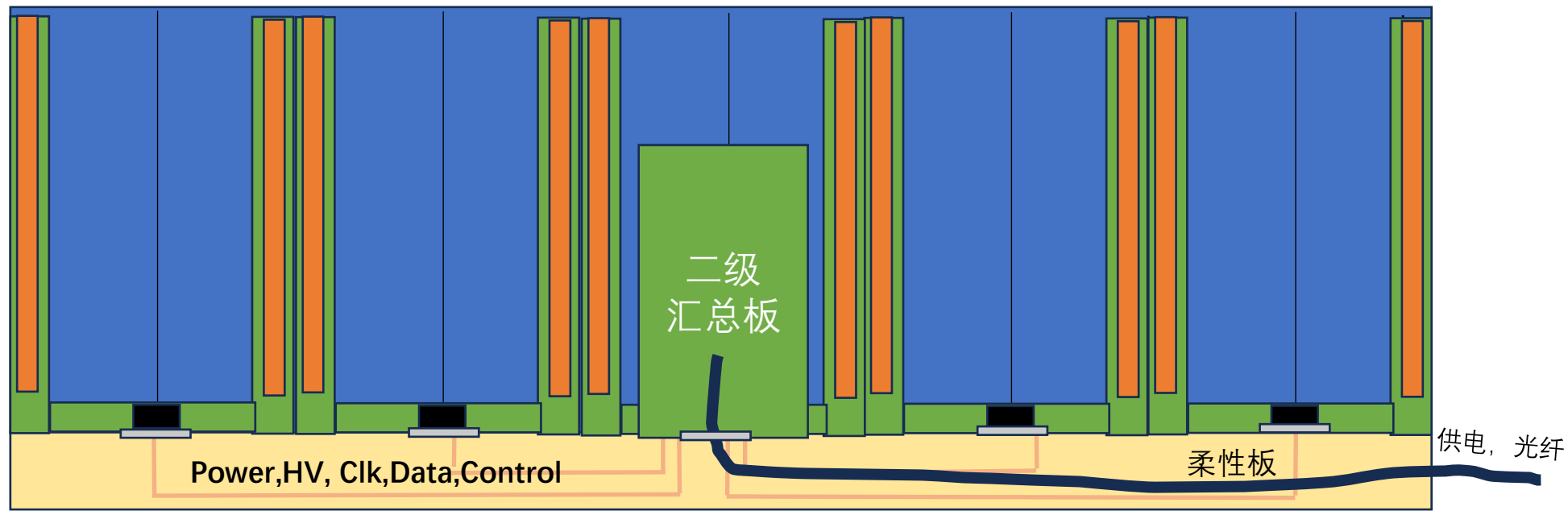
LGAD Barrel information

	LGAD
信息需求	TOA, TOT, 给触发?
Area (m ²)	~ 70
Granularity	70mm × 0.1mm (10平方厘米, 每个芯片128道)
Capacitance	~10 pF
Charge	>15fC
Channel number	~ 1×10^7 (10644480)
Module assembly	Wire bonding at strip
MIP Time resolution	~50 ps
Spatial resolution	~ 10 μm
Number of Module	3780 (14cm*14cm)
Number of channels per module	2816 (22 芯片, 128道)
Data size	16 bit (9 TOT, 7 TOA) + channel(7bit, 128) +bunch ID(8bit) + chip ID (4-5 bit) ~40-48 bits
Event rate	5Hz/ cm ²
散热/功耗上限	?

LGAD ele layout方案



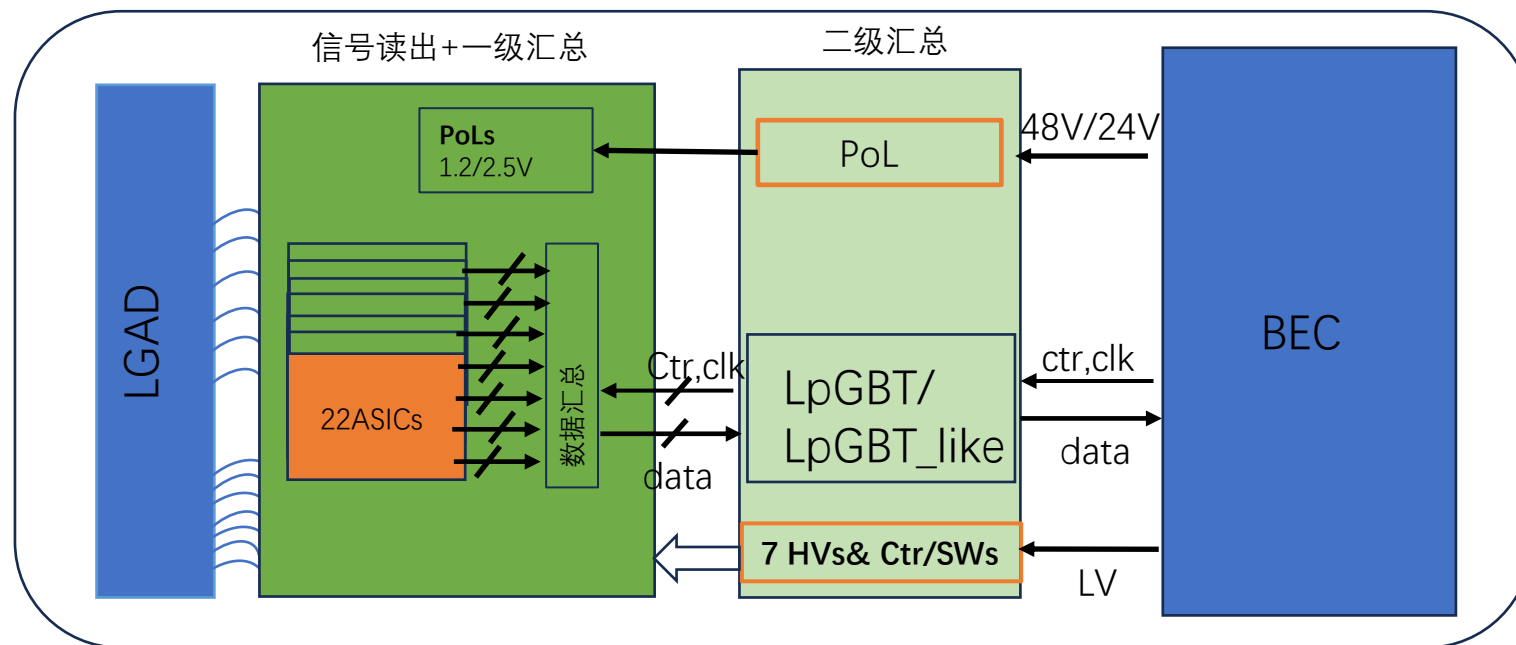
■ LGAD ■ PCB ■ ASIC ■ 一级汇总、供电 ■ 柔性板



系统方案 (适用LGAD & Si Strip)

- LGAD
- 数据汇总及传输, LpGBT, 光纤
- 高压(<800V)及控制:单独**高压控制**, **低压转高压**
- 触发?

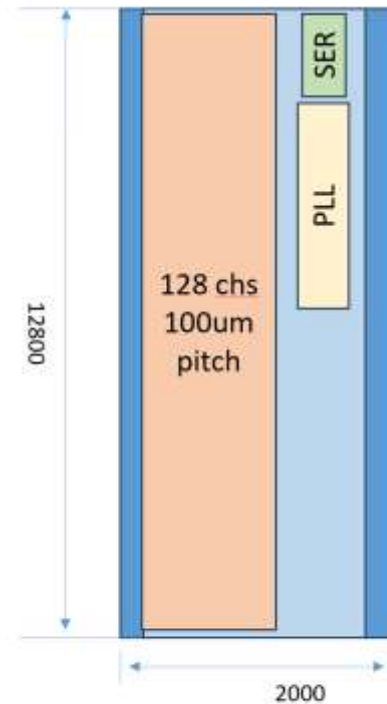
- Si Strip
- 数据汇总及传输, LpGBT, 光纤
- 高压(500V)及控制:同一高压, 单独**开关控制**
- 触发?



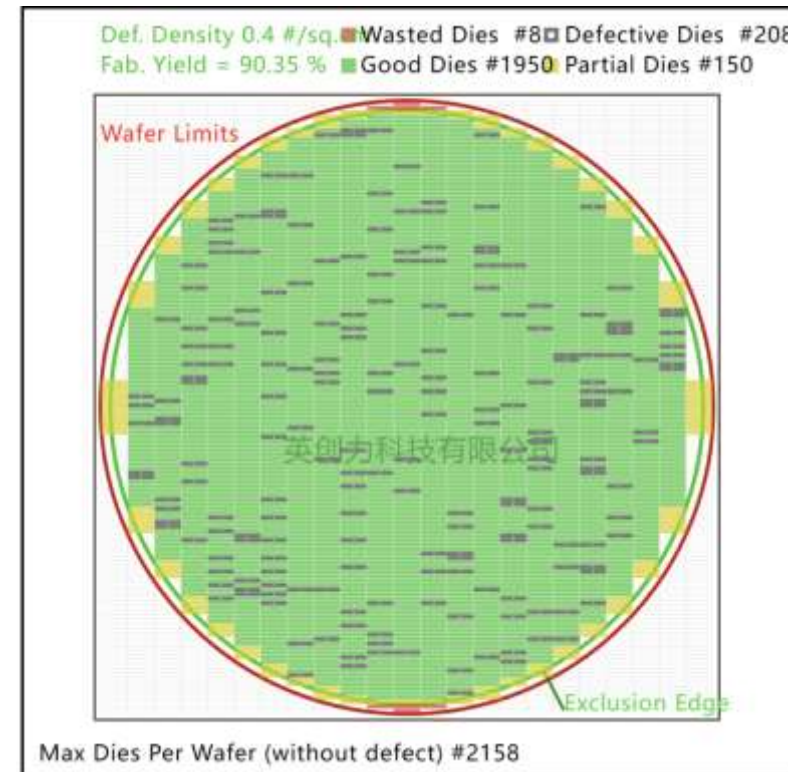
- 数据汇总芯片, 自研
- 若没有可用的高压模块, 直接每个module通过电缆给高压
- 若LpGBT无法采购, 自研LpGBT_like芯片系列

LGAD Data rate

	ASIC chs /chip	Chips /module	Modules /stave	Staves /ladder	Ladder	Total chip N	Total ch	Data rate/chip	Data bits	Data rate/stave	Total data rate
LGAD	128	22	7	6	90	84K/45 wafer	10644480	50Hz	48 bit	370Kbps	200Mbps



工艺: 55nm
 芯片尺寸: 12.8mm*2mm
 12寸wafer产量 (yield 90%): 1900 chips



Cost (LGAD)

Items	Unit	Unit cost (RMB)	Quantity	Total cost (10k RMB)	备注
FEE板PCB	块	200	3780	76	
FEE ASIC (8mm*3mm)	通道	0.09	1.06E7	190	
二级汇总板+柔性板	块	700	540	38	
光纤	根 (20m)	200	540	10	
Connector (光纤)	对	2000	540	110	
Connector (柔性板)	对 (1m)	100	3780	40	
Cables(1LV+10HV)	根 (20m)	400	540	22	
Total				486	
Necessary R&D	Type			1460	FEE ASIC, 数据汇总ASIC, 高压模块, LpGBT_like,

7modules*6 staves* 90ladders=3780 modules

假设PoL和LpGBT能买到, total计算未含数据汇总芯片, 高压模块

ASIC价格根据 SMIC 55nm计算, 工程批价格360万, 量产后价格2万/wafer

不含封装和打线

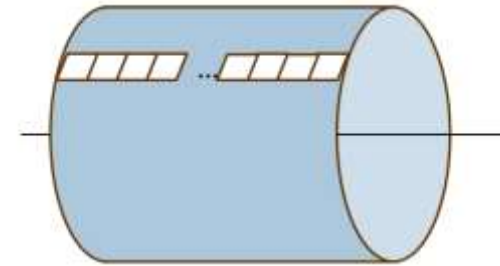
Arrangement of Si-Strip

➤ 114 ladders

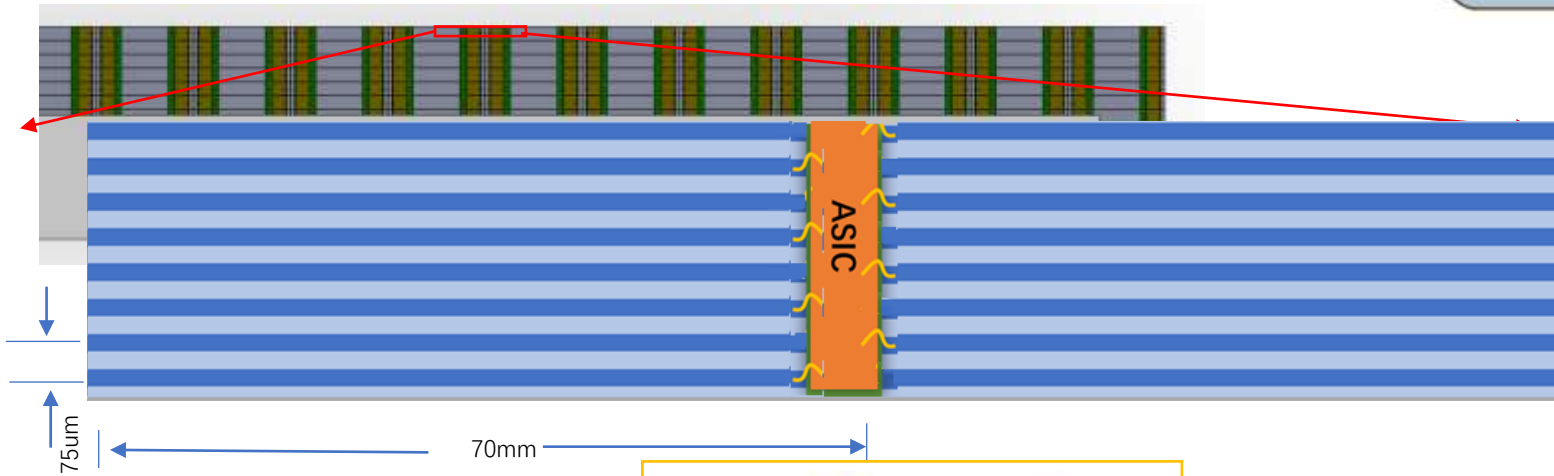
- ◆ 58 modules/ladder
 - 10 ASIC/module
 - ✓ 128 channels/ASIC

- Total modules needed:
 $114 * 58 = 6612$ modules

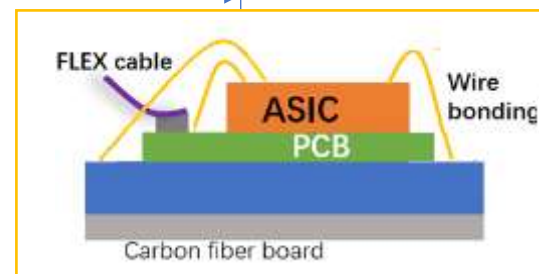
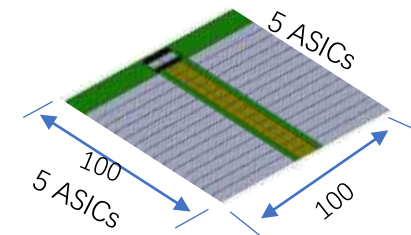
R= 1800 mm
H ~ 5808mm



Ladder



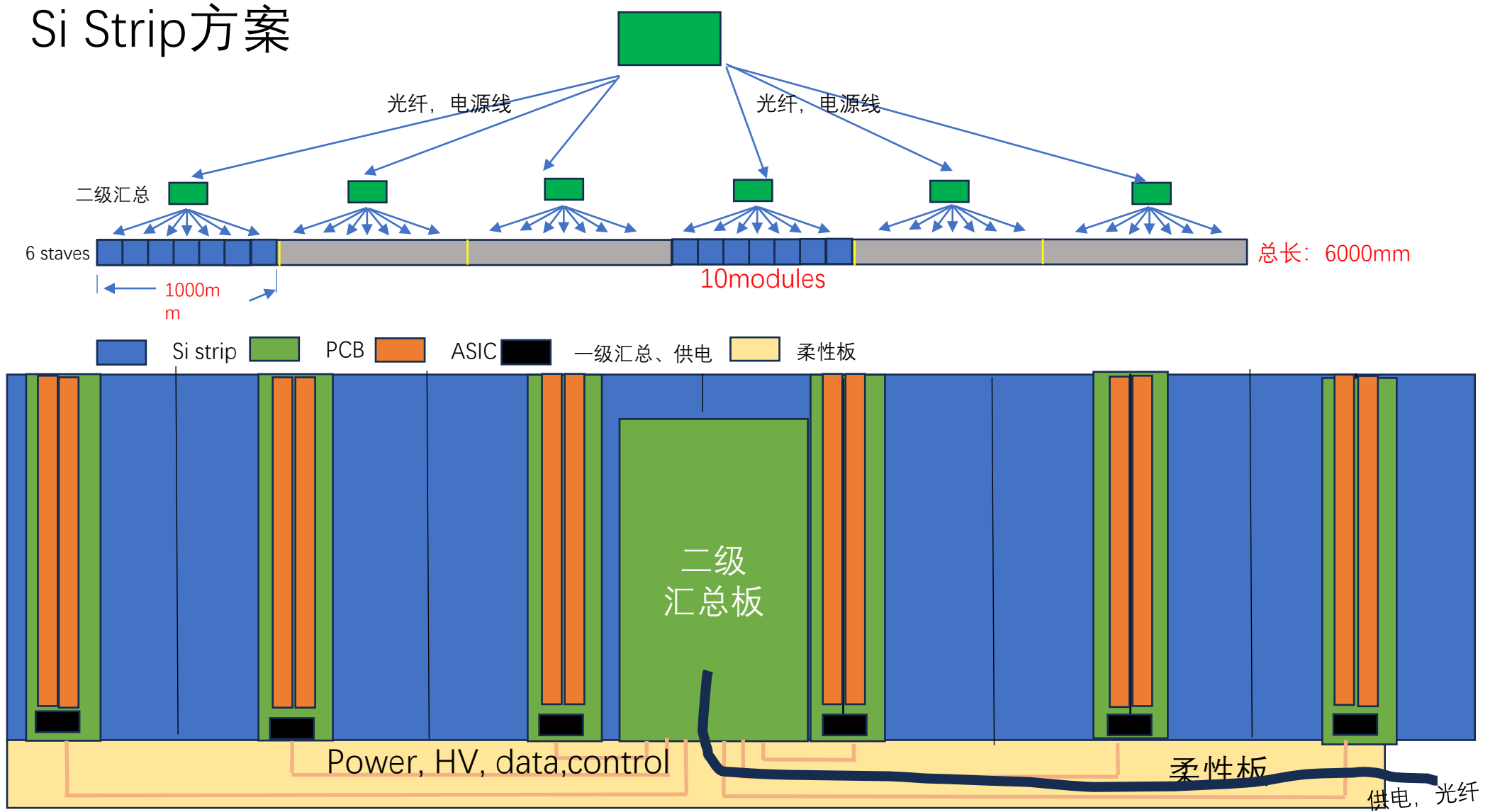
Module
100mm x 100mm



Si Strip Barrel

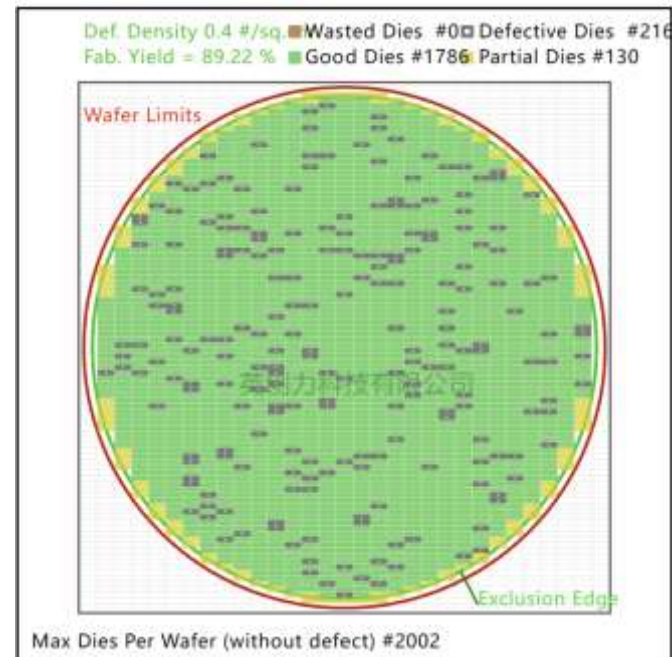
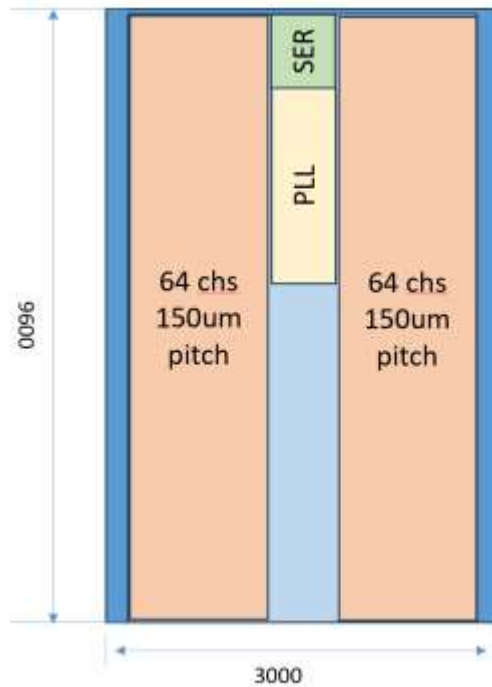
	Si Strip
信息需求	击中, 触发?
Area (m ²)	~66
Granularity	100mm × 0.075mm
Capacitance	2pF?
Charge	6 fC
Channel number	8.5 × 10⁶
Module assembly	wire bonding
MIP Time resolution	
Spatial resolution	
Number of Module	6610
Number of channels per module	1280
Data size	Hit + channel(7bit, 128) + bunch ID(8bit) + chip ID (4-5 bit) ~32 bit
Event rate	0.1Hz/条
散热/功耗上限	?

Si Strip方案



Si Trip Data rate

	ASIC chs /chip	Chips /module	Modules /stave	Staves /ladder	ladder	Total chip N	Total ch	Data rate/chip	Data bits	Data rate/stave	Total data rate
Si Strip	128	10	10	6	114	67K/38 wafer	8,460,800	12.8Hz	32 bit	41Kbps	27Mbps



工艺: 55nm
 芯片尺寸: 9.6mm*3mm
 12寸wafer产量 (yield 90%): 1800 chips

Cost (Si Strip)

Items	Unit	Unit cost (RMB)	Quantity	量产 成本 (10k RMB)	备注
FEE板PCB	块	200	6840	136	
FEE ASIC (6.4mm*3mm)	通道	0.09	8.7E6	176	
汇总版+柔性板(1m)	块	700	684	48	
光纤	根	200	684	14	
Connector (光纤)	对	2000	684	140	
Connector (柔性板)	对	100	6840	70	
Cables(1 LV+7HV)	根(20m)	400	684	28	
Total				612	
Necessary R&D	Type			1460	FEE ASIC, 数据汇总ASIC, 高压模块, LpGBT_like,

10modules*6 staves* 114 ladders=6840 modules

假设PoL和LpGBT能买到, total计算未含数据汇总芯片, 高压开关

ASIC价格根据 SMIC 55nm 12 inch wafer计算, 工程批360万+2万/片wafer

不含封装和打线

backup

Cost (1 GAD)

Items	Unit	Unit cost (RMB)	Quantity	自研成本	Total cost (10k RMB)	备注
FEE板PCB	块	100	3780		38	
FEE ASIC (8mm*3mm)	通道	0.09	1.06E7	360	90(流片)+100(测试) (45 wafer)	
PoL for module	个	100?	3780		38	多系统用
数据汇总芯片 (module)			3780	300		
汇总版+柔性板	块	400	540		22	
PoL for slave	个	100?	540		6	多系统用
高压模块 (300V)	个	?	3780	300		
高压控制模块	个	50	3780	300	20	
LpGBT_like	个			500		多系统应用
LpGBT	个	200?	540		10	市场价格
光纤	根 (20m)	200	540		10	
Connector (光纤)	对	2000	540		110	
Connector (柔性板)	对 (1m)	100	3780		40	
Cables(1LV+10HV)	根 (20m)	400	540		22	
Total					506	

7modules*6 staves* 90ladders=3780 modules

ASIC价格根据 SMIC 55nm计算, 工程批价格360万, 量产后价格2万/wafer

不含封装和打线

Cost (Si Strip)

Items	Unit	Unit cost (RMB)	Quantity	自研成本	量产成本 (10k RMB)	备注
FEE板PCB	块	100	6840		68	
FEE ASIC (6.4mm*3mm)	通道	0.09	8.7E6	360	76(流片)+100 (测试) (38 wafer)	
POL for module	个	100?	6840		68	
数据汇总芯片 (module)	片		6840	300		多系统应用
汇总版+柔性板(1m)	块	400	684		27	
POL for slave	个	100?	684		7	
高压开关	个	?	6840	300		PGA26E19BA停产
LpGBT_like及接口 LpGBT	个	200	684	500	14	多系统应用 市场价格
光纤	根	200	684		14	
Connector (光纤)	对	2000	684		140	
Connector (柔性板)	对	100	6840		70	
Cables(1 LV+7HV)	根(20m)	400	684		28	
Total					612	

10modules*6 staves* 114 ladders=6840 modules

高压开关: PGA26E19BA停产

ASIC价格根据 SMIC 55nm 12 inch wafer计算, 工程批360万+2万/片wafer

高压电缆: 外径>1.8mm

Construction			
Component	Material	Detail	Diameter
Centre conductor	Steel, Copper + Silver plated	Strand-07	0.31 mm
Dielectric	PTFE (Polytetrafluoroethylene)		0.83 mm
Outer conductor	Copper, Silver plated	Braid, 95%	1.33 mm
Jacket	FEP (Fluorinated ethylene propylene)	RAL 6015 - br	1.8 mm +/- 0.1 mm

Electrical data	
Impedance	50 Ω +/-2Ω
Operating frequency	≤ 3 GHz
Capacitance	97 pF/m
Velocity of signal propagation	69 %
Signal delay	4.84 ns/m
Screening effectiveness	40 dB at frequency 0.0001 GHz ... 1GHz
Insulation resistance	100000000 MΩ*m
Inner conductor resistance	742 Ω/km
Operating Voltage (at sea level)	≤ 0.5 kVrms
Test voltage (50 Hz/1 min)	≤ 1 kVrms

455-SUCOFORM_86_75

SUCOFORM_86_75

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25	¥104.6267	¥2,615.67
50	¥99.5078	¥4,975.39
100	¥94.4567	¥9,445.67
1,000	¥92.1854	¥92,185.40
2,500	报价	

Construction			
Component	Material	Detail	Diameter
Centre conductor	Steel, Copper + Silver plated	Wire	0.29 mm
Dielectric	PTFE (Polytetrafluoroethylene)		1.65 mm
Outer conductor	Copper, Tin plated	Tin soaked braid, 100%	2.1 mm

Electrical data	
Impedance	75 Ω +/-3Ω
Operating frequency	≤ 4 GHz
Capacitance	62 pF/m
Velocity of signal propagation	71 %
Signal delay	4.7 ns/m
Screening effectiveness	100 dB at frequency 0.1 GHz ... 4GHz
Insulation resistance	100000000 MΩ*m
Inner conductor resistance	680 Ω/km
Operating Voltage (at sea level)	≤ 1.5 kVrms
Test voltage (50 Hz/1 min)	≤ 3 kVrms

Mechanical data	
Weight	approx. 14 g/m
Static bending radius	≥ 6 mm
Repeated bending radius	20 mm (bendings, up to 50)